

1. General Description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Extended temperature range T_i = 175 °C
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Tin-plated 100% solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

	cici cii ce data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-12	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-3.2	А
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = -4.5 V; I _D = -3.2 A; T _j = 25 °C		-	100	122	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

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5. Pinning information

Table 2. P	inning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		
2	D	drain		
3	G	gate		
4	S	source		G (T
5	D	drain	3 8 4	
6	D	drain	Transparent top view	
7	D	drain	DFN2020MD-6 (SOT1220)	S 017aaa259
8	S	source		017444259

6. Ordering information

Table 3. Ordering information Type number Package Name Description Version BUK4D122-20P DFN2020MD-6 plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body SOT1220

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK4D122-20P	6н

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8. Limiting values

Table 5. Limiting values

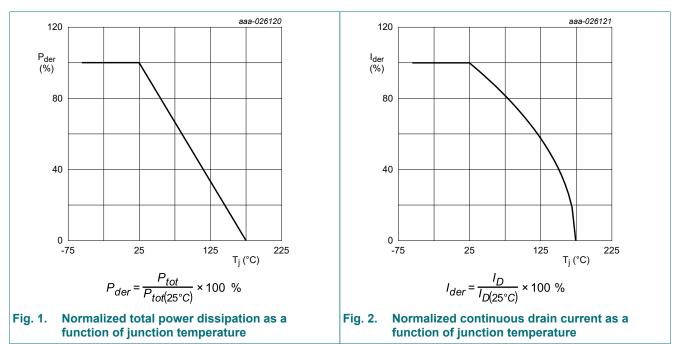
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-3.2	А
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2	A
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-13	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	550	mW
			[1]	-	1.95	W
		T _{sp} = 25 °C		-	10	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	T _{j(init)} = 25 °C; I _D = -0.5 A; DUT in avalanche (unclamped)		-	5	mJ
Source-drain	n diode					_
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.9	А
ESD maximu	ım rating	•				
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

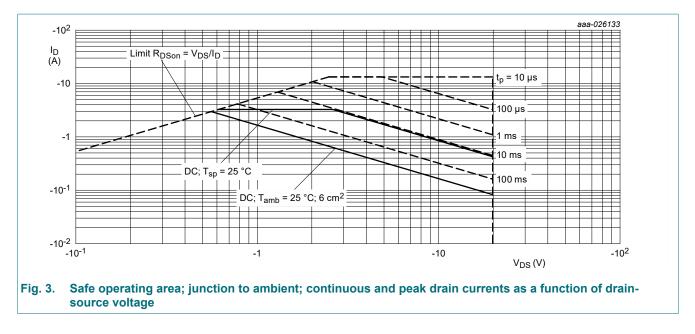
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

[2] Device mounted on an FR4[3] Measured between all pins.



20 V, P-channel Trench MOSFET

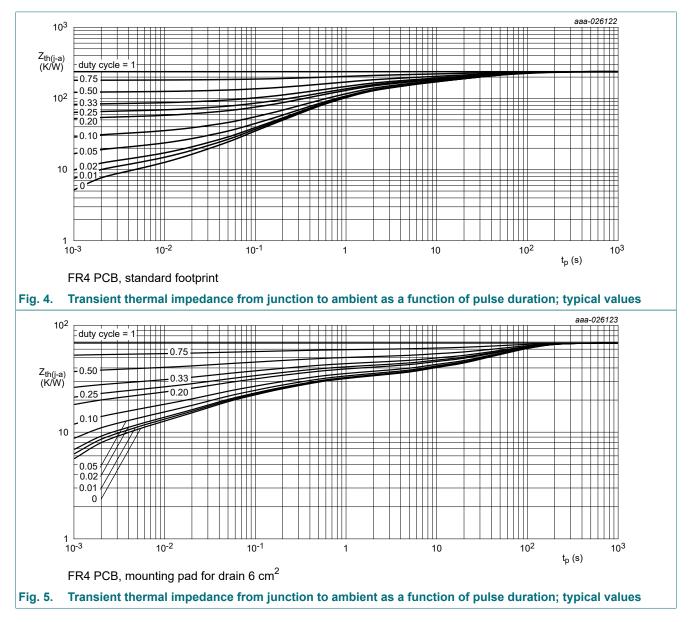


9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from	in free air	[1]	-	- 236	272	K/W
		[2]	-	67	77	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	12	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

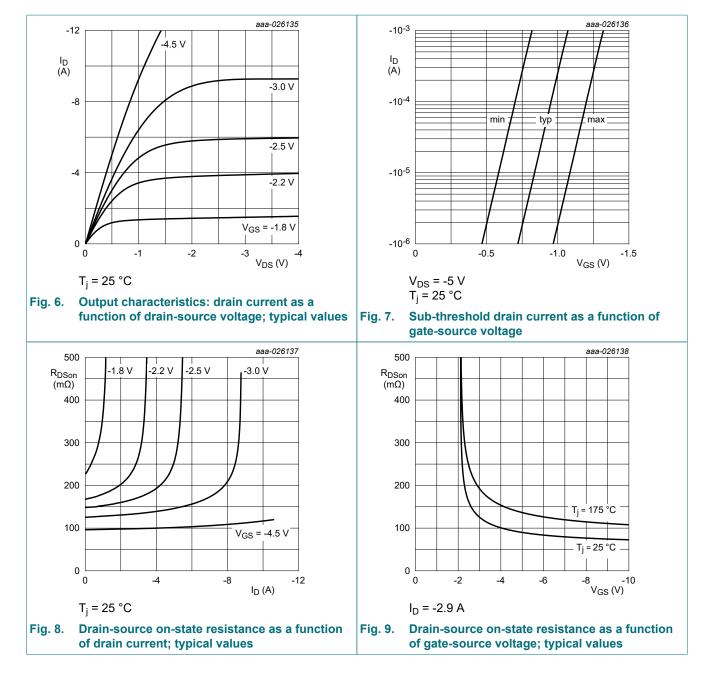
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



10. Characteristics

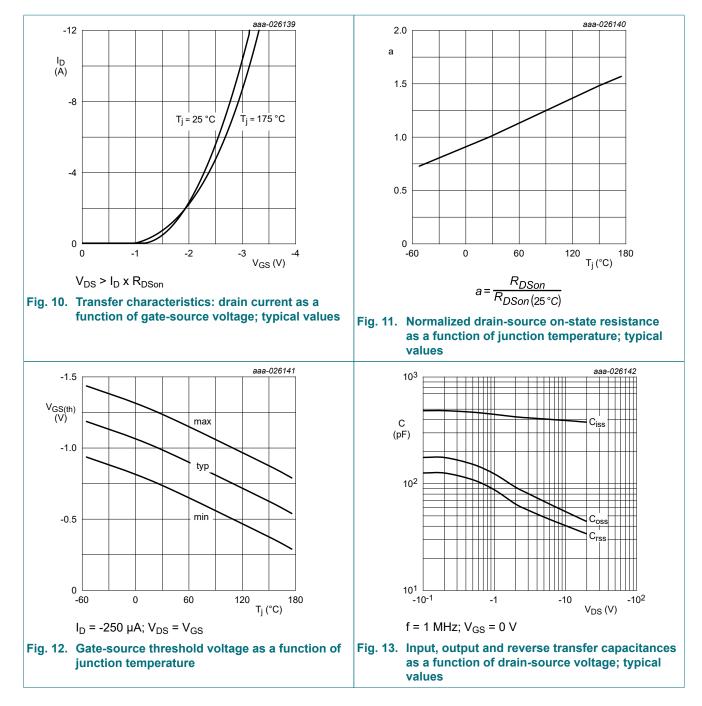
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	octeristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = -250 μA; V _{GS} = 0 V; T _j = 25 °C	-20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.75	-1	-1.25	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
R _{DSon}	drain-source on-state	V _{GS} = -4.5 V; I _D = -3.2 A; T _j = 25 °C	-	100	122	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -3.2 A; T _j = 175 °C	-	157	191	mΩ
		V _{GS} = -3 V; I _D = -2.6 A; T _j = 25 °C	-	125	190	mΩ
9fs	forward transconductance	V _{DS} = -10 V; I _D = -3.2 A; T _j = 25 °C	-	7	-	S
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	-	18.6	-	Ω
Dynamic ch	aracteristics	· · ·	I			
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I _D = -3.2 A; V _{GS} = -4.5 V;	-	3.3	5	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.8	-	nC
Q _{GD}	gate-drain charge	1 –	-	0.8	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	388	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	56	-	pF
C _{rss}	reverse transfer capacitance		-	39	-	pF
d(on)	turn-on delay time	V_{DS} = -10 V; I _D = -2.6 A; V _{GS} = -4.5 V;	-	5	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
d(off)	turn-off delay time	1	-	36	-	ns
t _f	fall time		-	17	-	ns
Source-drai	n diode	· · ·	I			
V _{SD}	source-drain voltage	I _S = -1.9 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.9	-1.2	V
t _{rr}	reverse recovery time	I _S = -1.9 A; dI _S /dt = 100 A/μs;	-	13.7	-	ns
Q _r	recovered charge	V _{GS} = 0 V; V _{DS} = -10 V; T _j = 25 °C	-	4.5	-	nC

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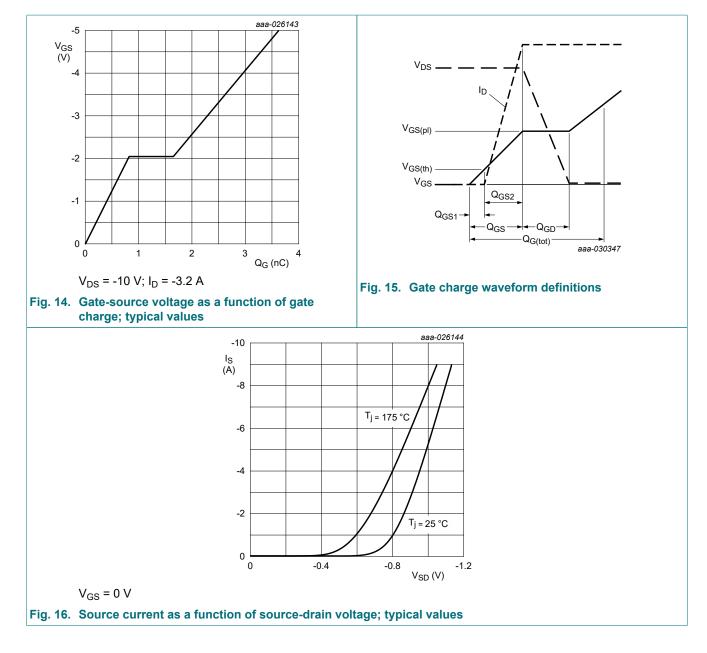
Product data sheet

20 V, P-channel Trench MOSFET



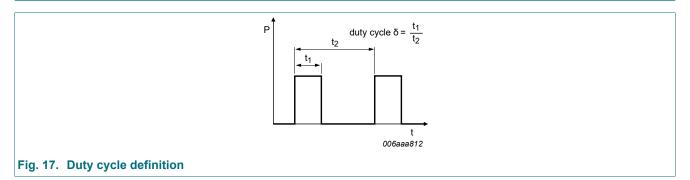
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20 V, P-channel Trench MOSFET



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11. Test information

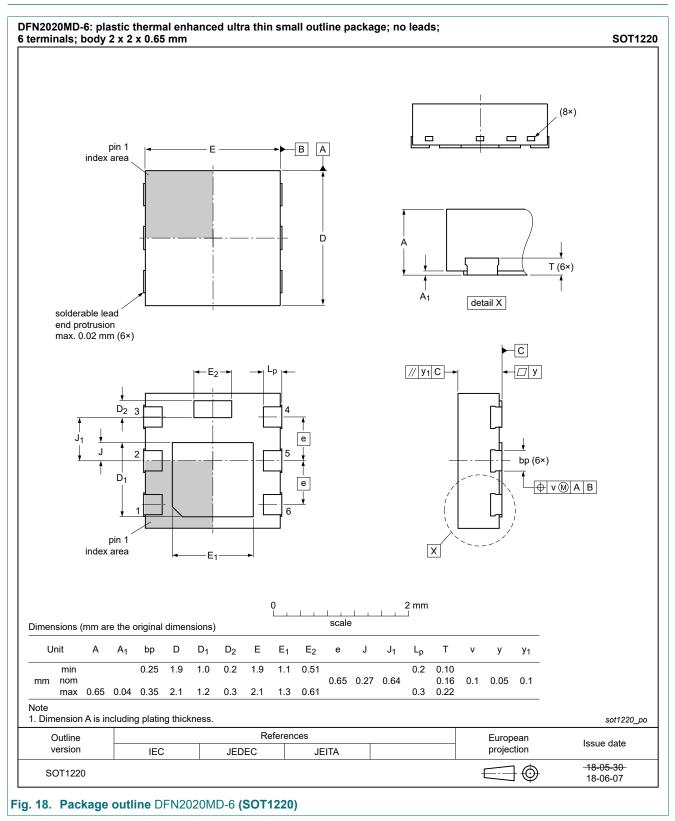


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

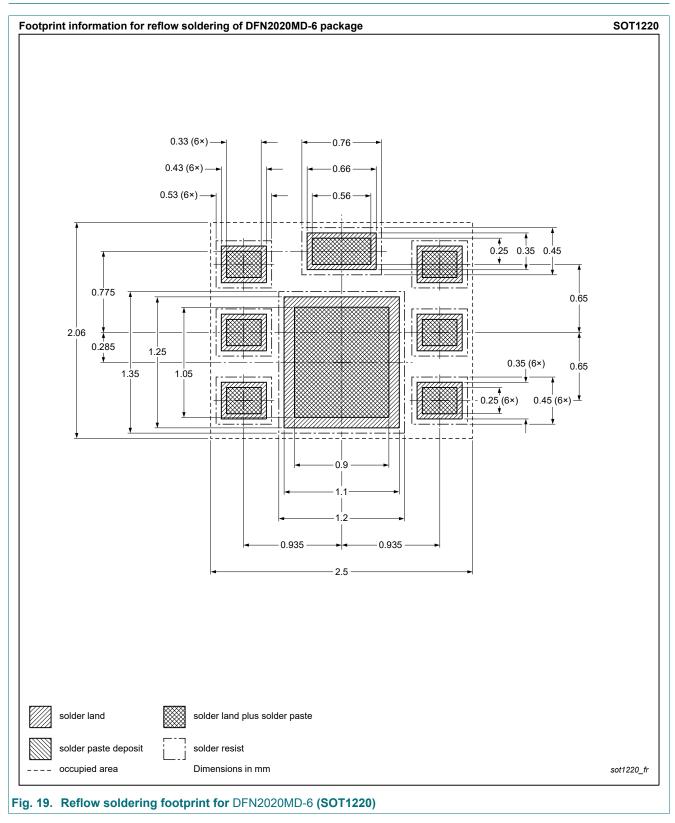
20 V, P-channel Trench MOSFET

12. Package outline



20 V, P-channel Trench MOSFET

13. Soldering



14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BUK4D122-20P v.2	20230327	Product data sheet	-	BUK4D122-20P v.1			
Modifications:	Complete rework	·					
BUK4D122-20P v.1	20200708	Product data sheet	-	-			

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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20 V, P-channel Trench MOSFET

Contents

1.	General Description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10.	Characteristics	6
11.	. Test information	10
12.	. Package outline	11
	Soldering	
14.	. Revision history	13
15.	Legal information	14
	-	

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